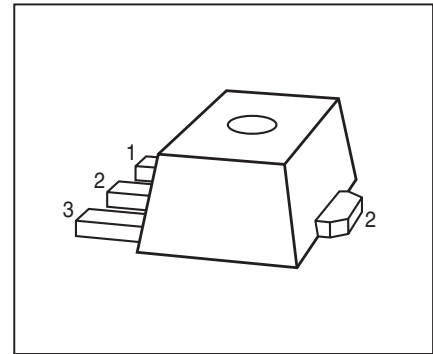


PNP Silicon AF Transistors

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary type: BCX68 (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration			Package
BCX69-10	CF	1=B	2=C	3=E	SOT89
BCX69-16	CG	1=B	2=C	3=E	SOT89
BCX69-25	CH	1=B	2=C	3=E	SOT89

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	20	V
Collector-base voltage	V_{CBO}	25	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	1	A
Peak collector current, $t_p \leq 10$ ms	I_{CM}	2	
Base current	I_B	100	mA
Peak base current	I_{BM}	200	
Total power dissipation- $T_S = 114$ °C	P_{tot}	3	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 12	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

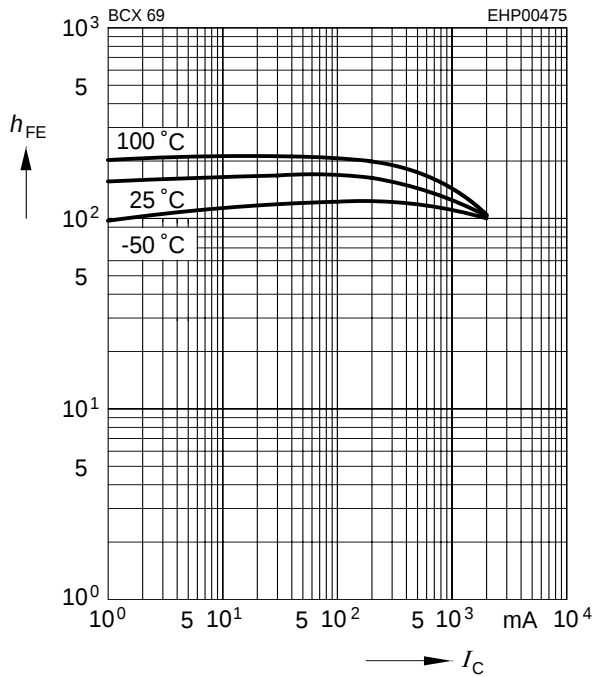
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 30\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	20	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$	$V_{(BR)CBO}$	25	-	-	
Emitter-base breakdown voltage $I_E = 1\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 25\text{ V}$, $I_E = 0$ $V_{CB} = 25\text{ V}$, $I_E = 0$, $T_A = 150$	I_{CBO}	- -	- -	0.1 100	μA
DC current gain ¹⁾ $I_C = 5\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}$, $V_{CE} = 1\text{ V}$, BCX69-10 $I_C = 500\text{ mA}$, $V_{CE} = 1\text{ V}$, BCX69-16 $I_C = 500\text{ mA}$, $V_{CE} = 1\text{ V}$, BCX69-25 $I_C = 1\text{ A}$, $V_{CE} = 1\text{ V}$	h_{FE}	50 85 100 160 60	- 100 160 250 -	- 160 250 375 -	-
Collector-emitter saturation voltage ¹⁾ $I_C = 1\text{ A}$, $I_B = 100\text{ mA}$	V_{CEsat}	-	-	0.5	V
Base-emitter voltage ¹⁾ $I_C = 5\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 1\text{ A}$, $V_{CE} = 1\text{ V}$	$V_{BE(ON)}$	- -	0.6 -	- 1	
AC Characteristics					
Transition frequency $I_C = 100\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 20\text{ MHz}$	f_T	-	100	-	MHz

¹⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

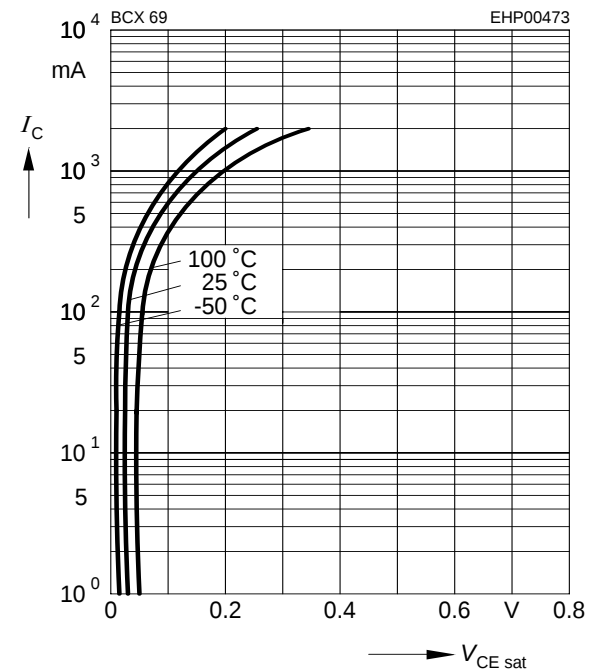
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1 \text{ V}$



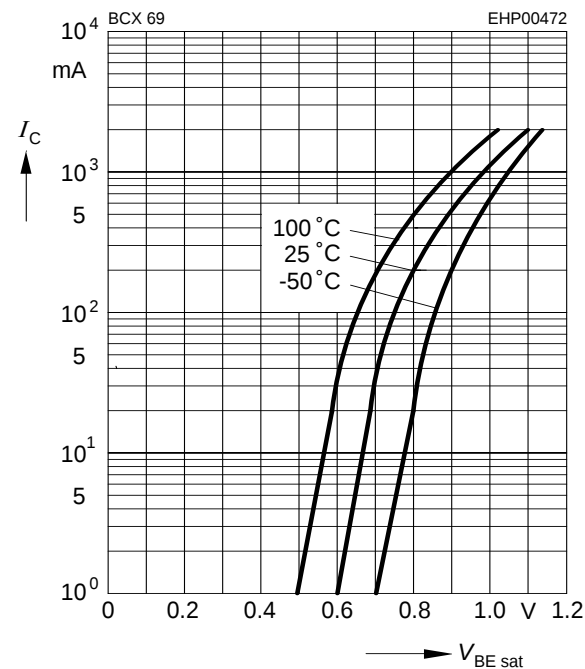
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 10$



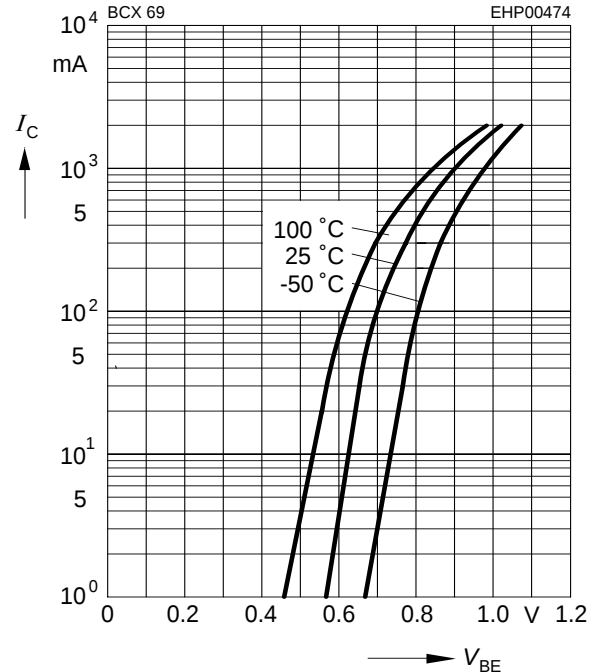
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 10$



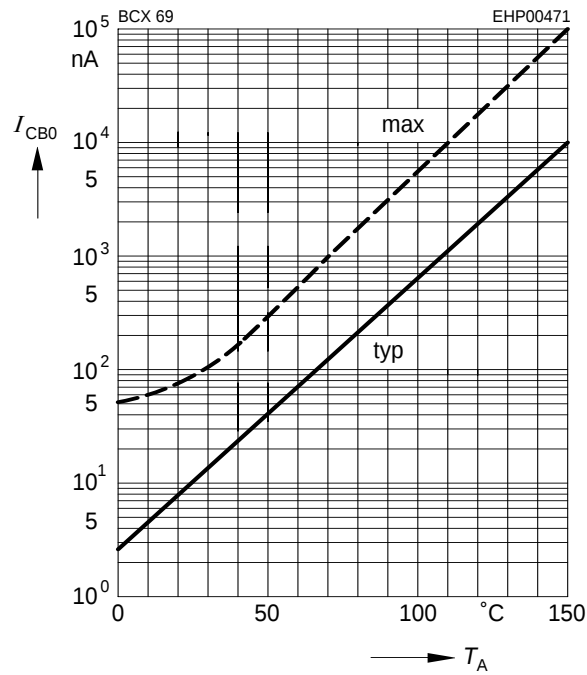
Collector current $I_C = f(V_{BE})$

$V_{CE} = 1 \text{ V}$



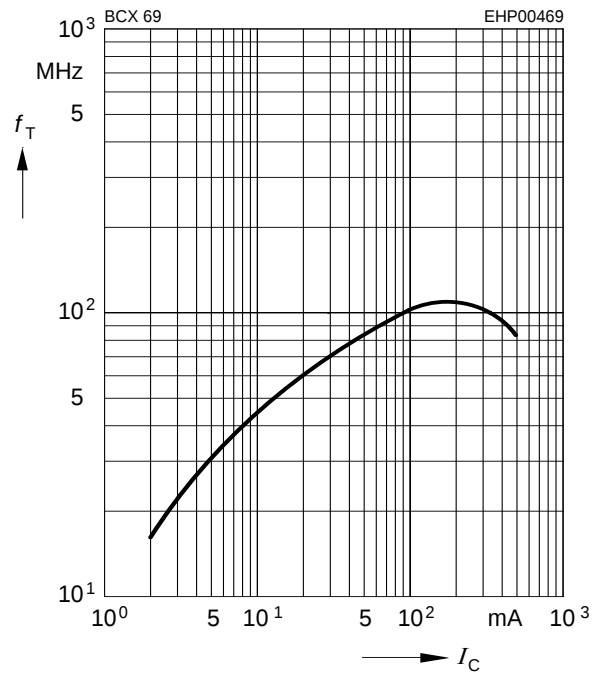
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CB} = 25 \text{ V}$

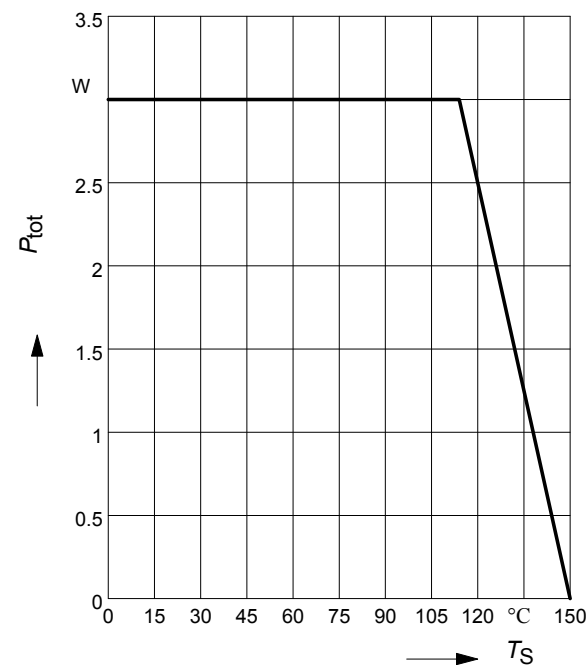


Transition frequency $f_T = f(I_C)$

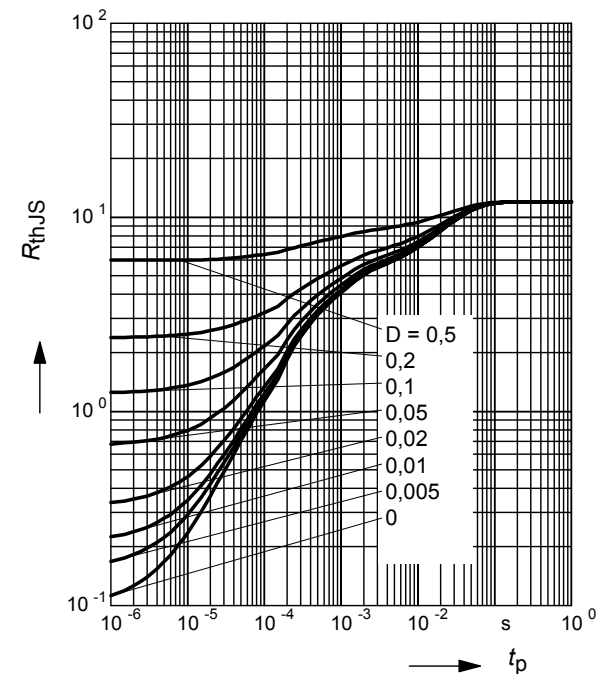
$V_{CE} = 5 \text{ V}$



Total power dissipation $P_{tot} = f(T_S)$

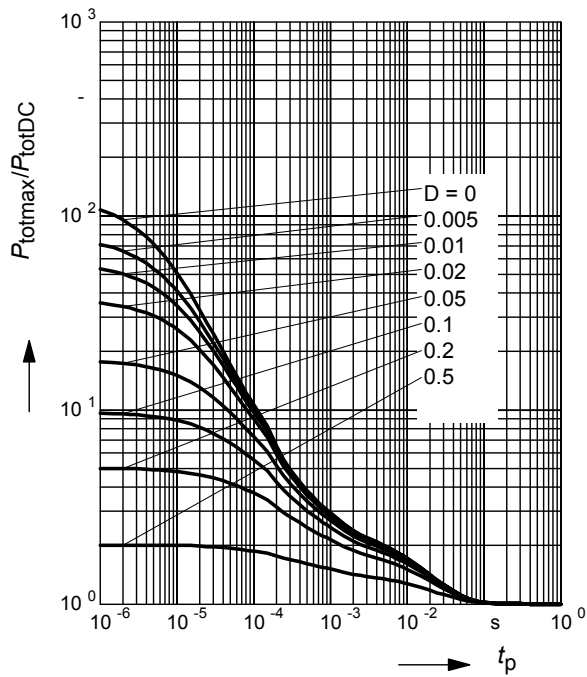


Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$



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